Materials	Preparation	Current density/ Capacity/ Number of cycles	Voltage window	Configuration	Ref.
Multi-layered Ti ₂ CT _x	Immersion of Ti ₂ AlC in 10 % HF at RT for 10 h	1 C, 110 mAh g ⁻¹ , 80; 10 C, 70 mAh g ⁻¹ , 200	0.05 to 2.5 V	Half-cell	154
TiO ₂ /Ti ₂ CT _x	Immersion of HF-etched multi-layered Ti_2CT_x in 30 wt. % H_2O_2 for 5 min	100 mA g ⁻¹ , 389 mAh g ⁻¹ , 50; 500 mA g ⁻¹ , 337 mAh g ⁻¹ , 100; 1000 mA g ⁻¹ , 280 mAh g ⁻¹ , 1000	0.005 to 3.0 V	Half-cell	68
Cu ₂ O/Ti ₂ CT _x	Hydrothermal synthesis of HCl/LiF-prepared Ti ₂ CT _x with stoichiometric amount of Cu(CH ₃ COO) ₂ .H ₂ O at 150 °C for 10 h	1000 mA g ⁻¹ , 143 mAh g ⁻¹ , 250	0.05 to 2.5 V	Half-cell	155
Free-standing "paper" of Ti ₃ C ₂ T _x *	Typical HF etching, followed by DMSO-intercalation, sonication and filtration	1C, 410 mAh g ⁻ 1, 700; 36 C, 110 mAh g ⁻¹ , 700	0 to 2.5 V	Half-cell	31
Free-standing disc of 90 wt. % Ti ₃ C ₂ T _x /CB*	Immersion of Ti_3AlC_2 in 50 % HF at RT for 18 h, $Ti_3C_2T_x$ powders cold pressed at 1 GPa	C/3 (30 mA g ⁻¹), 97 mAh g ⁻¹ , 5.9 mAh cm ⁻ ²(areal capacity), 50	0.005 to 3.0 V	Half-cell	156
Porous 90 wt. % Ti ₃ C ₂ T _x / MWCNTs*	Filtration of mixture of acid treated, partial oxidized HCl/LiF-prepared Ti ₃ C ₂ T _x as catalysed by Cu ²⁺ , and MWCNTs	160 mA g ⁻¹ , ca. 800 mAh g ⁻¹ , 350	0.01 to 3.0 V	Half-cell	75
86.2 wt. % Ti ₃ C ₂ T _x /CNFs	Liquid-phase impregnation of HF-etched $Ti_3C_2T_x$ with PVP: Co(NO ₃) ₂) (mass ratio- 1: 10), followed by CVD at 600°C for 0.5 h in Ar with acetylene	320 mA g ⁻¹ , 320 mAh g ⁻ ¹ , 300; 100 C, 97 mAh g ⁻¹ , 2900	0.01 to 3.0 V	Half-cell	58
PVP-Sn(IV)@ Ti ₃ C ₂ T _x	Intercalation of HF-etched $Ti_3C_2T_x$ with LiOH, followed by immersion in 1 M SnCl ₄ with 0.1g of PVP at RT for 24 h then dried	500 mA g ⁻¹ , 544 mAh g ⁻ ¹ , 200	0.01 to 3.0 V	Half-cell	59
90 wt.% Ti ₃ C ₂ T _x /Ag	Direct reduction of 50 mg of AgNO ₃ in the presence of 100 mg of HF-etched $Ti_3C_2T_x$ and 100 mL of DI water	1 C (320 mA g ⁻¹), 310 mAh g ⁻¹ , 800; 10 C, 260 mAh g ⁻¹ , 1000 50 C, 150 mAh g ⁻¹ , 5000	0.01 to 3.0 V	Half-cell	78

Table S1 A summary of various MXenes and their electrochemical performances as LIBs anode materials. (*) denotes the binder-free.

Table S1 Continued.

Materials	Preparation	Current density/ Capacity/ Number of cycles	Voltage window	Configuration	Ref.
Free-standing film of 50 wt. % Ti ₃ C ₂ T _x /planar NiCo ₂ O ₄	Alternatively spray coating of delaminated HCl/LiF Ti ₃ C ₂ T _x and NiCo ₂ O ₄ dispersions	1 C, 1010 mAh g ⁻¹ , 100	0.01 to 3.0 V	Half-cell	157
Multi-layered Nb ₂ CT _x	Immersion of Nb ₂ AIC in 50 % HF at RT for 90 h	1 C, 170 mAh g ⁻¹ , 150; 10 C, 110 mAh g ⁻¹ , 150	0 to 2.5 V	Half-cell	15
Free-standing film of 90 wt. % Nb ₂ CT _x /MWCNTs *	Immersion of Nb ₂ AlC in 50 % HF at 55 °C for 48 h, R- NH ₃ ⁺ intercalation, sonication; filtration of mixture of delaminated HF- etched Nb ₂ CT _x and MWCNTs	0.5 C, 420 mAh g ⁻¹ , 100; 2.5 C, 430 mAh g ⁻¹ , 300; 10 C, ca. 220 mAh g ⁻¹ , 100	1.0 to 3.0 V	Half-cell	47
Free-standing disc of 90 wt. % Nb ₂ CT _x /CB*	Immersion of Nb ₂ AlC in 50 % HF at 55 °C for 40 h, Nb ₂ CT _x powders cold pressed at 1 GPa	30 mA g ⁻¹ , 128 mAh g ⁻¹ , 6.7 mAh cm ⁻² (areal capacity), 50	0.005 to 3.0 V	Half-cell	156
Free-standing "paper" of 90 wt. % Nb ₂ CT _x - MWCNTs	Immersion of Nb ₂ AlC in 50 % HF at 55 °C for 48 h, TBAOH-intercalation, sonication and filtration of mixture with MWCNTs	50 mA g ⁻¹ , ca. 270 mAh g ⁻¹ , 100	0.01 to 3.0 V	Half-cell	158
Free-standing "paper" of 90 wt. % Nb ₂ CT _x - MWCNTs*	As above	250 mA g ⁻¹ , ca. 27 mAh g ⁻¹ , 540	0.01 to 3.0 V	Full-cell (with lithiated graphite as anode)	158
Free-standing "paper" of 90 wt. % Nb ₂ CT _x - MWCNTs*	As above	250 mA g ⁻¹ , ca. 12 mAh g ⁻¹ , 540	3.3 to 0.3 V	Full-cell (with pre-cycled LiFePO₄ as cathode)	158
Free-standing "paper" of 90 wt. % Nb ₂ CT _x - MWCNTs*	As above	250 mA g ⁻¹ , ca. 20 mAh g ⁻¹ , 940	0.01 to 3.0 V	Full symmetrical cell	158
Nb₂O₅@multi- layered Nb₄C₃T _x	Partial oxidation of HF- etched Nb ₄ C ₃ T _x at 850 °C for 0.5 h under CO ₂ flow rate of 75 sccm	0.25 C, 195 mAh g⁻¹, 400	0.05 to 2.0 V	Half-cell	63

Table S1 Continued.

Materials	Preparation	Current density/ Capacity/ Number of cycles	Voltage window	Configuration	Ref.
Multi-layered V_2CT_x	Immersion of V ₂ AIC or attrition-milled V ₂ AIC in 50 % HF at RT for 90 h or 8 h respectively	1 C, 210 to 260 mAh g ⁻¹ , 150; 10 C, 125 mAh g ⁻¹ , 150	0 to 3.0 V	Half-cell	15
Free-standing "paper" of Mo ₂ TiC ₂ T _x *	Immersion of Mo ₂ TiAlC ₂ in 50 % HF at 55 °C for 48 h, DMSO-intercalation, sonication and filtration	1 C, 145 mAh g ⁻¹ , 160	0.02 to 3.0 V	Half-cell	17
Free-standing "paper" of 92 wt. % Mo ₂ CT _x - MWCNTs*	Immersion of Mo ₂ Ga ₂ C in 14M HF at 55 °C for 6.6 days, TBAOH-intercalation, sonication and alternating filtration with MWCNTs	5 A g ⁻¹ , 250 mAh g ⁻¹ , 1000; 10 A g ⁻¹ , 76 mAh g ⁻¹ , 1000	0.005 to 3.0 V	Half-cell	32

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Materials	Preparation	Volumetric capacitance, Gravimetric capacitance	Scan rate or current density	Voltage window	Configuration	Ref.
Delaminated Ti₃C₂T _x	Immersion of Ti ₃ AlC ₂ 6 M in HCl with LiF added, at 40 °C for 45 h	900 F cm ⁻³ , 245 F g ⁻¹	2 mV s ⁻¹	-0.3 to 0.25 V	Three-electrode system, activated carbon counter electrode, Ag/AgCl/1 M KCl reference electrode, 1 M H ₂ SO ₄ electrolyte	30
Delaminated Ti ₃ C ₂ T _x	Typical HF etching, followed by DMSO- intercalation, sonication	520 F cm ⁻³ , 325 F g ⁻¹ ; 415 F cm ⁻³	2 mV s ⁻¹ ; 5 A g ⁻¹	-0.4 to 0.2 V	As above	80
Delaminated Ti ₃ C ₂ T _x	Typical HF etching, followed by DMSO- intercalation, sonication	360 F cm ⁻³ ; 162 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻ 1	-0.8 to 0.1 V	Three-electrode system, activated carbon counter electrode, Ag/AgCl/1 M KCl reference electrode, 1 M MgSO ₄ electrolyte	55
Mixed 95 wt. % Ti ₃ C ₂ T _x /SWCNTs	Filtration of mixture of delaminated HF-etched Ti ₃ C ₂ T _x and SWCNTs	300 F cm ⁻³ ; 236 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻ 1	-0.8 to 0.1 V	As above	55
Sandwich-like 95 wt. % Ti ₃ C ₂ T _x / SWCNTs	Alternating filtration of delaminated HF-etched Ti ₃ C ₂ T _x and SWCNTs dispersions	390 F cm ⁻³ ; 280 F cm ⁻³ ; 345 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻¹ ; 5 A g ⁻¹	-0.8 to 0.1 V	As above	55
Mixed 95 wt. % Ti ₃ C ₂ T _x /MWCNTs	Filtration of mixture of delaminated HF-etched $Ti_3C_2T_x$ and MWCNTs	366 F cm ⁻³ ; 236 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻ 1	-0.8 to 0.1 V	As above	55

Table S2 A summary of various MXenes and their electrochemical performances as supercapacitor electrodes.

Table S2 Continued.

Materials	Preparation	Volumetric capacitance, Gravimetric capacitance	Scan rate or current density	Voltage window	Configuration	Ref.
Sandwich-like 95 wt. % Ti ₃ C ₂ T _x / MWCNTs	Alternating filtration, with MWCNTs dispersion used instead	321 F cm ⁻³ ; 250 F cm ⁻³ ; 350 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻¹ ; 10 A g ⁻¹	-0.8 to 0.1 V	As above	55
Sandwich-like 95 wt. % Ti ₃ C ₂ T _x /onion-like carbon (OLC)	Alternating filtration, with OLC dispersion used instead	397 F cm ⁻³ ; 218 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻ 1	-0.8 to 0.1 V	As above	55
Sandwich-like 95 wt. % Ti ₃ C ₂ T _x /rGO	Alternating filtration, with rGO dispersion used instead	435 F cm ⁻³ ; 320 F cm ⁻³ ; 370 F cm ⁻³	2 mV s ⁻¹ ; 200 mV s ⁻¹ ; 10 A g ⁻¹	-0.8 to 0.1 V	As above	55
92 wt. % Ti ₃ C ₂ T _x /PPy	Filtration of mixture of HCl/LiF- prepared Ti ₃ C ₂ T _x and PPy	1000 F cm ⁻³ , 416 F g ⁻¹	5 mV s ⁻¹	-0.2 to 0.35 V	Three electrode system, activated carbon counter electrode, Ag/AgCl reference electrode, 1 M H ₂ SO ₄ electrolyte	56
64.3wt. % PPy/ Ti ₃ C ₂ T _x	Electrophoretic deposition of HF-etched Ti ₃ C ₂ T _x , electrochemica I polymerization of PPy	291 F cm ⁻³ , 485 F g ⁻¹	1 mA cm ⁻ 2	0.0 to 0.5 V	Three electrode system, saturated calomel reference electrode, 0.5 M H ₂ SO ₄ electrolyte	162
Ti ₃ C ₂ T _x EMI-TFSI ionogel film	Filtration of mixture of HCl/LiF- prepared Ti ₃ C ₂ T _x , then immerse I EmI- TFSI electrolyte	62 F g ⁻¹	20 mV s ⁻¹	0.0 to 3.0 V	Two-electrode Swagelok symmetric cell, EMI-TFSI electrolyte	163
80 wt. % Ti ₃ C ₂ T _x /MWCNTs	Filtration of mixture of HCl/LiF- prepared Ti ₃ C ₂ T _x and MWCNTs	245 F cm ⁻³ , 85 F g ⁻¹ ; 76 F g ⁻¹	2 mV s ⁻¹ ; 1 A g ⁻¹	-0.4 to -0.2 V	Three-electrode system, activated carbon counter electrode, Ag wire reference electrode, 1 M EMITFSI in acetonitrile	164

electrolyte

Table S2 (Continued.
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Materials	Preparation	Volumetric capacitance, Gravimetric capacitance	Scan rate or current density	Voltage window	Configuration	Ref.
Ti ₃ C ₂ T _x /MWCNTs	Filtration of mixture of delaminated HF-etched Ti ₃ C ₂ T _x and MWCNTs	393 F cm ⁻³	5 mV s ⁻¹	0.1 to 0.55 V	Three-electrode system, platinum counter electrode, Hg/HgO reference electrode, 6 M KOH electrolyte	165
TiO ₂ /HF-etched multi-layered Ti ₃ C ₂ T _x	In situ hydrolysis of TBOT within mixture of HF- etched multi- layered Ti ₃ C ₂ T _x , heat treatment	143 F g ⁻¹	5 mV s ^{.1}	-1.0 to -0.35 V	Three-electrode system, platinum counter electrode, Ag/AgCl/3 M KCl reference electrode, 6 M KOH electrolyte	71
50 wt. % ε- MnO₂/Ti₃C₂T _x	Impregnation of HF- etched Ti ₃ C ₂ T _x with MnSO ₄ at 60 °C then oxidized with KMnO ₄	211 F g ⁻¹ ; 212 F g ⁻¹	10 mV s ⁻ ¹ ; 1 A g ⁻¹	0.0 to 0.7 V	Two-electrode symmetric cell, in 30 wt. % KOH electrolyte	166
MnO ₂ /Ti ₃ C ₂ T _x	Addition of Mn(NO ₃) ₂ and KMnO ₄ to HF- etched Ti ₃ C ₂ T _x , followed by sintering at 300 °C for 3 h in N ₂	130 F g ⁻¹	5 mV s ⁻¹	-1.0 to -0.4 V	Three-electrode system, platinum counter electrode, Ag/AgCl/3 M KCl reference electrode, 6 M KOH electrolyte	167
38 wt. % delaminated HF- etched Ti ₃ C ₂ T _x /nickel- aluminium layered double hydroxide composite	Addition of Ni- containing parent solution, H_3BO_3 and Al(NO_3) ₃ to delaminated HF-etched Ti ₃ C ₂ T _x , stirred for 48 h at 50 °C	1061 F g ⁻¹ ; 556 F g ⁻¹	1 A g ⁻¹ ; 10 A g ⁻¹	0.0 to 0.6 V	Three-electrode system, platinum counter electrode, saturated calomel reference electrode, 6 M KOH electrolyte	168

Table S2 Continued.

Materials	Preparation	Volumetric capacitance, Gravimetric capacitance	Scan rate or current density	Voltage window	Configuration	Ref.
All solid-state HCl/LiF etched Ti ₃ C ₂ T _x (ca. 1 μ m), with a PVA/H ₂ SO ₄ gel electrolyte	Sequential spray-coating HCl/LiF etched Ti ₃ C ₂ T _x (3–6 μ m) and HCl/LiF etched Ti ₃ C ₂ T _x (1 μ m), drip casting of PVA/H ₂ SO ₄ gel electrolyte	357 F cm ^{−3}	20 mV s ⁻¹	0 to 0.6 V	Two-electrode, symmetrical all solid- state HCl/LiF etched Ti ₃ C ₂ T _x microsupercapacitors	169
Free-standing "paper" of delaminated HF- etched Mo ₂ TiC ₂ T _x *	Immersion of Mo ₂ TiAlC ₂ in 50 % HF at 55 °C for 48 h, DMSO- intercalation, sonication and filtration	413 F cm ⁻³	2 mV s ⁻¹	-0.1 to 0.4 V	Three-electrode system, activated carbon counter electrode, Ag/AgCl/1 M KCl reference electrode, 1 M H ₂ SO ₄ electrolyte	17
Free-standing "paper" of delaminated HF- etched Mo ₂ CT _x *	Immersion of Mo ₂ Ga ₂ C in 14M HF at 55 °C for 6.6 days, TBAOH- intercalation, sonication and filtration	196 F g ⁻¹	2 mV s ⁻¹	-0.30 to 0.30 V	Three-electrode system, activated carbon counter electrode, Ag/AgCl/1 M KCl reference electrode, 1 M H ₂ SO ₄ electrolyte	32
Orthorhombic Nb ₂ O ₅ /amorphou s carbon/Nb ₂ CT _x	Partial oxidation of HF-etched Nb ₂ CT _x at 850 °C for 1h in CO ₂	275 F g ⁻¹	5 mV s ⁻¹	-1.95 to 0 V	Three-electrode system, activated carbon counter electrode, AgCl coated Ag wire as reference electrode, 1 MLiClO ₄ /EC/DMC electrolyte	64

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